Title (en)

TRENCH-GATE MOS TRANSISTOR, ITS USE IN AN EEPROM DEVICE AND PROCESS FOR MANUFACTURING THE SAME

Title (de)

GRABEN-GATE-MOS-TRANSISTOR, DESSEN VERWENDUNG IN EINER EEPROM-ANORDNUNG UND VERFAHREN ZU DESSEN HERSTELLUNG

Title (fr)

TRANSISTOR MOS A GRILLE ET TRANCHEE, SON UTILISATION DANS DES SYSTEMES DE MEMOIRES MORTES PROGRAMMABLES EFFA ABLES ELECTRIQUEMENT, ET SON PROCEDE DE PRODUCTION

Publication

EP 1060518 A1 20001220 (DE)

Application

EP 99911574 A 19990127

Priority

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Abstract (en)

[origin: WO9943029A1] A first source-drain zone (471), a second source/drain zone (472) and an intermediate channel (44) are arranged in a semiconductor substrate (41). The surface of the channel (44) is provided with a gate dielectric (45). A gate electrode (46) is arranged in the channel (44) and is at the most as long as the channel (44) is deep. Gate dielectric (45) and gate electrode (46) are thus buried in the channel (44) and the MOS transistor is suitable as embedded MOS transistor, in particular for EEPROM devices.

IPC 1-7

H01L 29/78; H01L 21/336; H01L 29/423

IPC 8 full level

H01L 21/336 (2006.01); **H01L 21/8247** (2006.01); **H01L 27/115** (2017.01); **H01L 27/11521** (2017.01); **H01L 29/423** (2006.01); **H01L 29/78** (2006.01)

CPC (source: EP)

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